

20 V, P-channel Trench MOSFET

17 May 2019

Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic-level compatible
- Trench MOSFET technology
- Very fast switching
- AEC-Q101 qualified

3. Applications

- Relay driver
- High-speed line driver
- High-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V _{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-	-4.1	А
Static charact	eristics						
R _{DSon}	drain-source on-state resistance	V _{GS} = -4.5 V; I _D = -2.4 A; T _j = 25 °C		-	48	55	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².



5. Pinning information

Table 2	. Pinning in	formation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain		D
2	D	drain		
3	G	gate		G-UP
4	S	source	TSOP6 (SOT457)	s
5	D	drain		017aaa257
6	D	drain		

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMN48XPA	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457			

7. Marking

Table 4. Marking codes

Type number	Marking code
PMN48XPA	ВА

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017aaa124

8. Limiting values

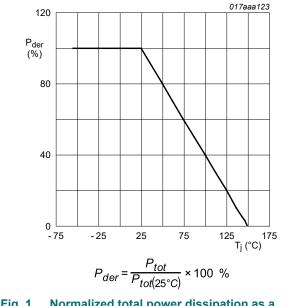
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V _{GS}	gate-source voltage	_		-12	12	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-4.1	А
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-2.5	A
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	-20	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	530	mW
			[1]	-	1.3	W
		T _{sp} = 25 °C		-	6.3	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	n diode					
ls	source current	T _{amb} = 25 °C	[1]	-	-1.4	А

Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².
 Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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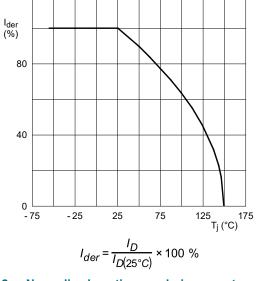
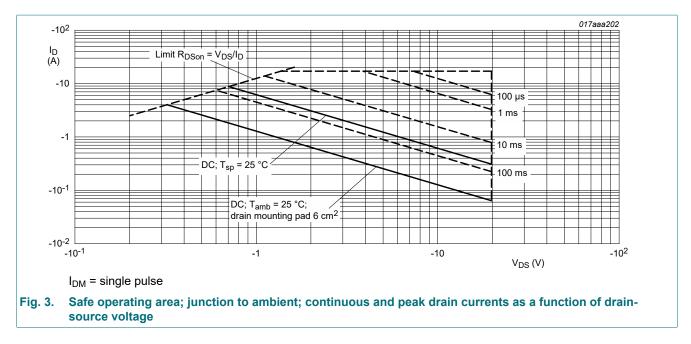


Fig. 1. Normalized total power dissipation as a function of junction temperature



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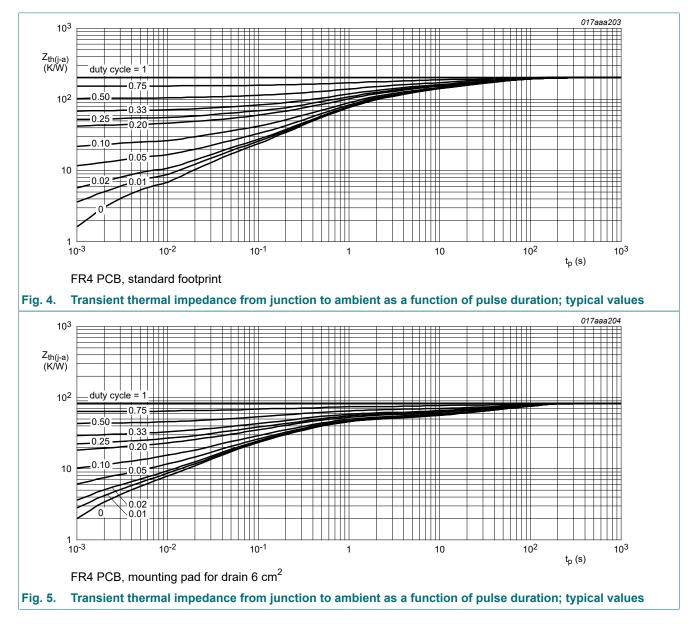


9. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
u (j-a)	thermal resistance from	in free air	[1]	-	204	235	K/W
	junction to ambient		[2]	-	84	97	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	17	20	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

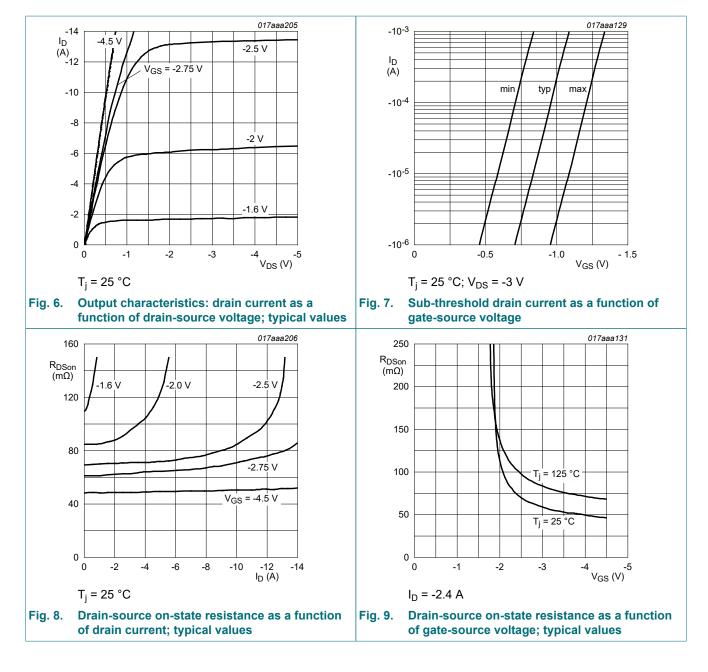
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².



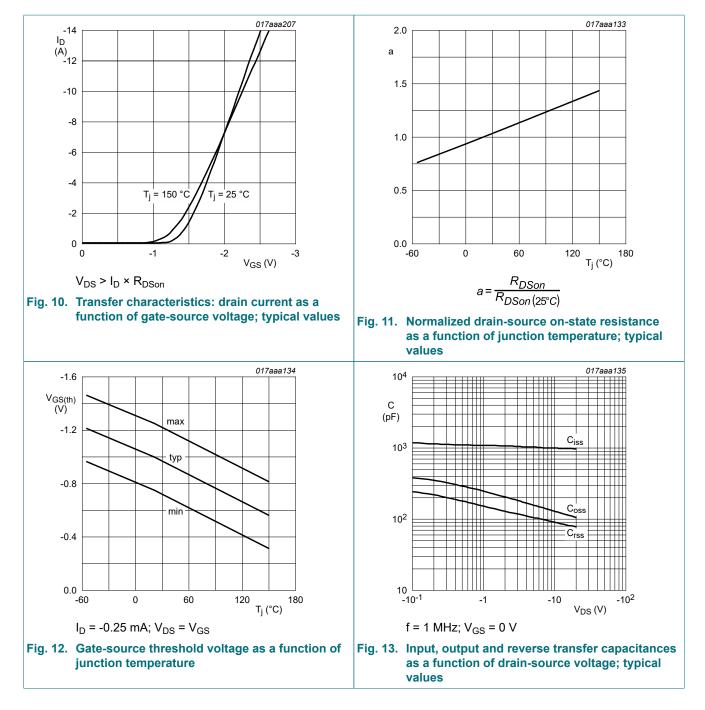
10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics		I	_		
V _{(BR)DSS}	drain-source breakdown voltage	I _D = -250 μA; V _{GS} = 0 V; T _j = 25 °C	-20	-	-	V
V _{GSth}	gate-source threshold voltage	I _D = -250 μA; V _{DS} =V _{GS} ; T _j = 25 °C	-0.75	-1	-1.25	V
I _{DSS}	drain leakage current	V _{DS} = -20 V; V _{GS} = 0 V; T _j = 25 °C	-	-	-1	μA
		V _{DS} = -20 V; V _{GS} = 0 V; T _j = 150 °C	-	-	-10	μA
I _{GSS}	gate leakage current	V _{GS} = -12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
R _{DSon}	drain-source on-state	V_{GS} = -4.5 V; I _D = -2.4 A; T _j = 25 °C	-	48	55	mΩ
	resistance	V _{GS} = -4.5 V; I _D = -2.4 A; T _j = 150 °C	-	70	80	mΩ
		V _{GS} = -2.5 V; I _D = -2 A; T _j = 25 °C	-	72	82	mΩ
9fs	forward transconductance	V _{DS} = -5 V; I _D = -2.4 A; T _j = 25 °C	-	10	-	S
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	V_{DS} = -10 V; I_D = -1 A; V_{GS} = -4.5 V;	-	8.7	13	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	1.8	-	nC
Q _{GD}	gate-drain charge		-	1.7	-	nC
C _{iss}	input capacitance	V _{DS} = -10 V; f = 1 MHz; V _{GS} = 0 V;	-	1000	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	130	-	pF
C _{rss}	reverse transfer capacitance		-	90	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = -10 V; I _D = -1 A; V _{GS} = -5 V;	-	15	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	22	-	ns
t _{d(off)}	turn-off delay time	1	-	51	-	ns
t _f	fall time	1	-	22	-	ns
Source-drai	n diode					
V _{SD}	source-drain voltage	I _S = -2.4 A; V _{GS} = 0 V; T _i = 25 °C	-	-0.75	-1	V

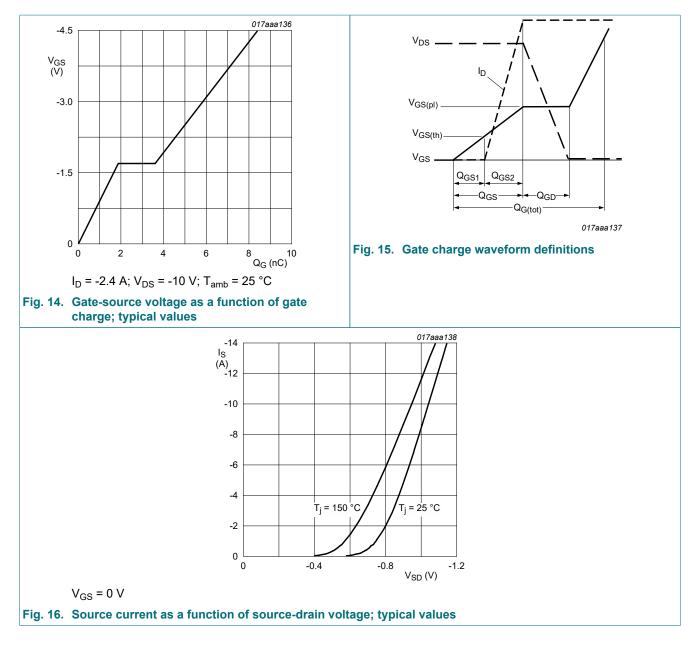
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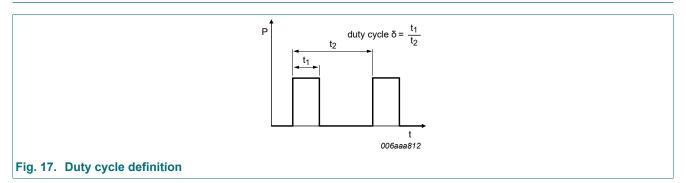
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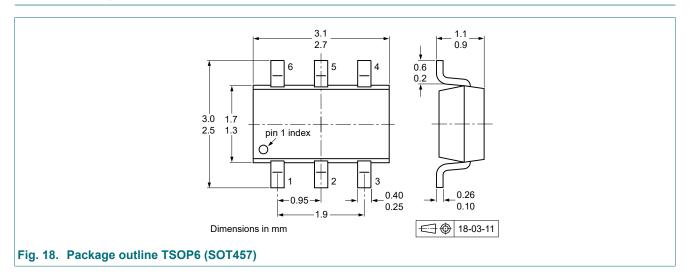
11. Test information



Quality information

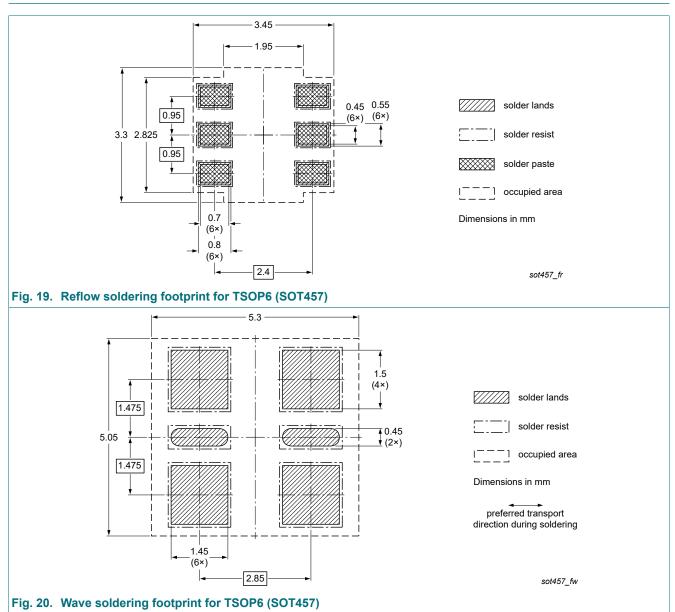
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline



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13. Soldering



14. Revision history

Table 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PMN48XPA v.1	20190517	Product data sheet	-	-		

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

- [2] The term 'short data sheet' is explained in section "Definitions".
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